

# CD4030B Types

## COS/MOS Quad Exclusive-OR Gate

High-Voltage Types (20-Volt Rating)

The RCA-CD4030B types consist of four independent Exclusive-OR gates. The CD4030B provides the system designer with a means for direct implementation of the Exclusive-OR function.

The CD4030B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ ) (Voltages referenced to $V_{SS}$ Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10$ mA
POWER DISSIPATION PER PACKAGE ( $P_D$ ):	
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F)	500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE ( $T_A$ ):	
PACKAGE TYPES D, F, H	-55 to $+125^\circ\text{C}$
PACKAGE TYPE E	-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE ( $T_{stg}$ )	-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79 mm) from case for 10 s max.	$+265^\circ\text{C}$

### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package Temperature Range)	3	18	V

### Features:

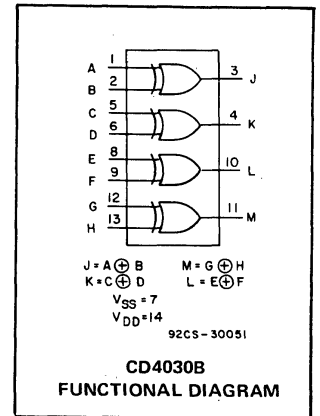
- Medium-speed operation— $t_{PHL}$ ,  $t_{PLH} = 65$  ns (typ.) at  $V_{DD} = 10$  V,  $C_L = 50$  pF
- 100% tested for quiescent current at 20 V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1  $\mu\text{A}$  at 18 V over full package-temperature range; 100 nA at 18 V and  $25^\circ\text{C}$
- Noise margin (over full package-temperature range):

1 V at  $V_{DD} = 5$  V

2 V at  $V_{DD} = 10$  V

2.5 V at  $V_{DD} = 15$  V

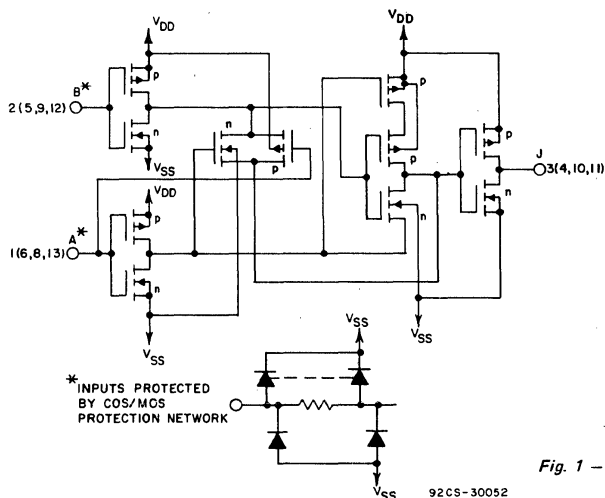
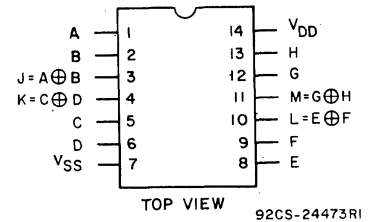
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"



### Applications:

- Even and odd parity generators and checkers
- Logical comparators
- Adders/subtractors
- General logic functions

### TERMINAL DIAGRAM Top View



### TRUTH TABLE FOR ONE OF FOUR IDENTICAL GATES

A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

I = HIGH LEVEL  
O = LOW LEVEL

Fig. 1 — Schematic diagram (1 of 4 identical gates).

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## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	Values at -55, +25, +125 Apply to D, F, H Packages				Values at -40, +25, +85 Apply to E Package			
				-55	-40	+85	+125	+25			
				Min.	Typ.	Max.					
Quiescent Device Current, I <sub>DD</sub> Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA
	—	0,10	10	2	2	60	60	—	0.02	2	
	—	0,15	15	4	4	120	120	—	0.02	4	
	—	0,20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current I <sub>OL</sub> Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I <sub>OH</sub> Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V <sub>OL</sub> Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V <sub>OH</sub> Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V <sub>IL</sub> Max.	0.5,4.5	—	5	1.5				—	—	1.5	V
	1,9	—	10	3				—	—	3	
	1.5,13.5	—	15	4				—	—	4	
Input High Voltage, V <sub>IH</sub> Min.	0.5,4.5	—	5	3.5				3.5	—	—	V
	1,9	—	10	7				7	—	—	
	1.5,13.5	—	15	11				11	—	—	
Input Current I <sub>IN</sub> Max.	—	0,18	18	±0.1	±0.1	±1	±1	—	±10 <sup>-5</sup>	±0.1	μA

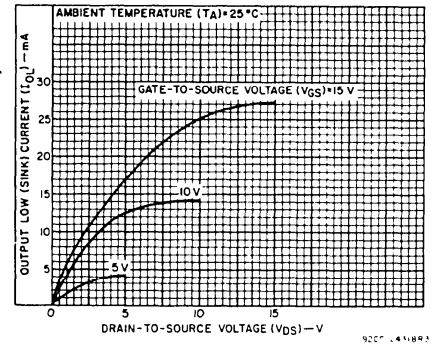


Fig. 2 - Typical output low (sink) current characteristics.

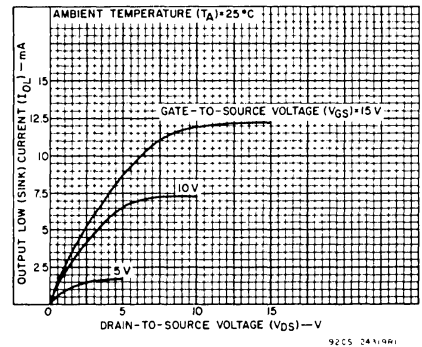


Fig. 3 - Minimum output low (sink) current characteristics.

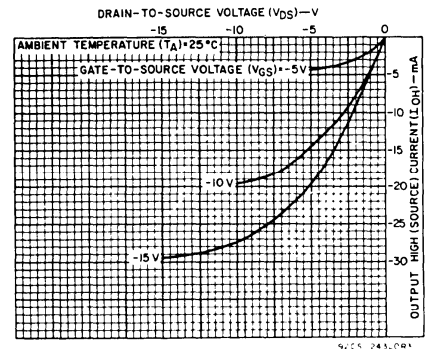


Fig. 4 - Typical output high (source) current characteristics.

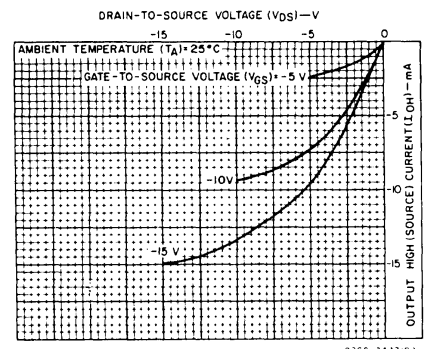


Fig. 5 - Minimum output high (source) current characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS at T<sub>A</sub> = 25°C; Input t<sub>r</sub>, t<sub>f</sub> = 20 ns, C<sub>L</sub> = 50 pF, R<sub>L</sub> = 200 kΩ

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS	
		V <sub>DD</sub> (V)			
			Typ.		Max.
Propagation Delay Time, t <sub>PLH</sub> , t <sub>PHL</sub>	Any Input	5	140	280	ns
		10	65	130	
		15	50	100	
Transition Time, t <sub>THL</sub> , t <sub>TLH</sub>	Any Input	5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C <sub>IN</sub>	Any Input	5	7.5	pF	

# CD4030B Types

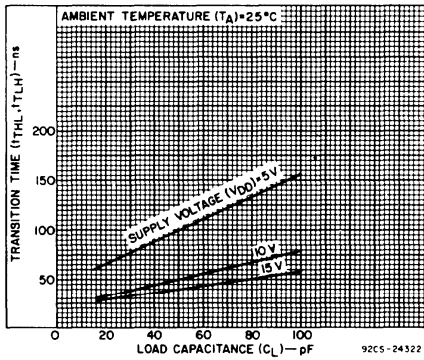


Fig. 6 - Typical transition time as a function of load capacitance.

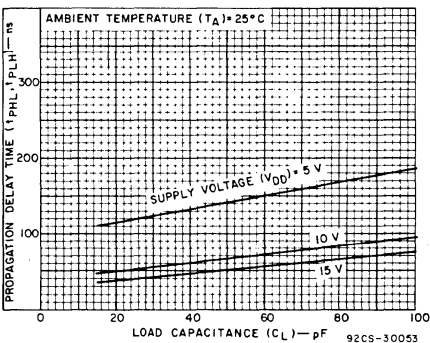


Fig. 7 - Typical propagation delay time as a function of load capacitance.

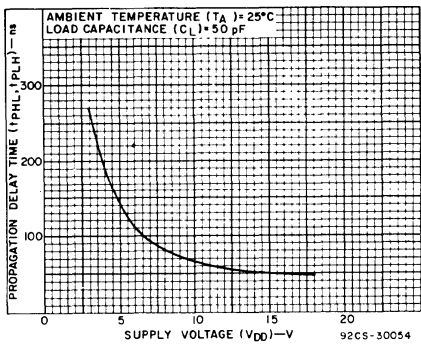


Fig. 8 - Typical propagation delay time as a function of supply voltage.

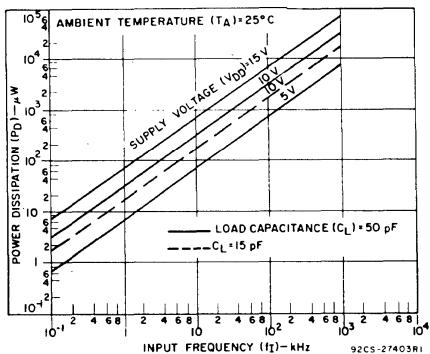


Fig. 9 - Typical dynamic power dissipation as a function of input frequency.

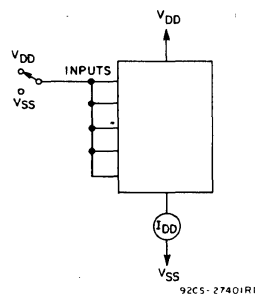


Fig. 10 - Quiescent-device current test circuit.

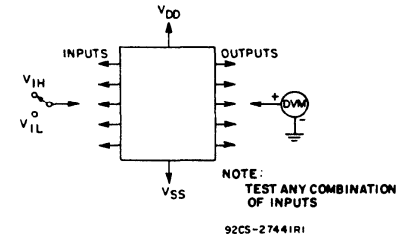


Fig. 11 - Input-voltage test circuit.

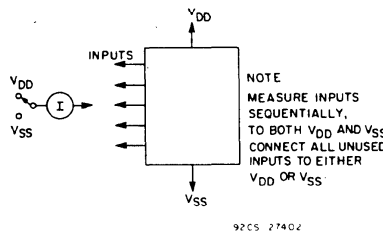


Fig. 12 - Input-current test circuit.

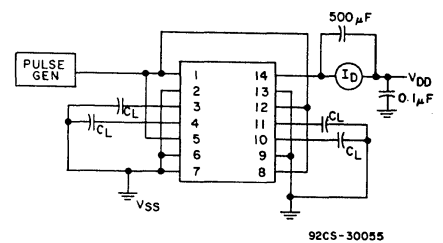
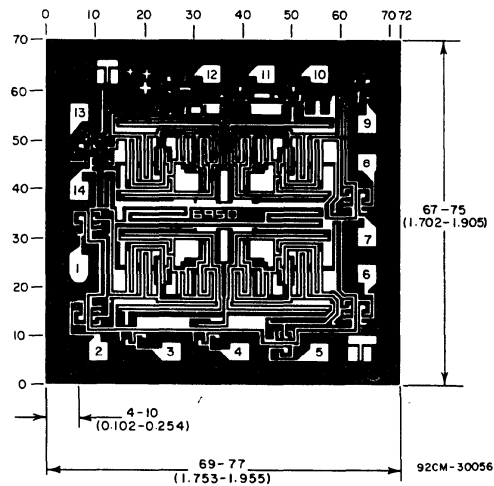


Fig. 13 - Dynamic power dissipation test circuit.



Dimensions and pad layout for CD4030BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).

The photographs and dimensions of each COS/MOS chip represent a chip when it is part of the wafer. When the wafer is cut into chips, the cleavage angles are  $57^\circ$  instead of  $90^\circ$  with respect to the face of the chip. Therefore, the isolated chip is actually 7 mils (0.17 mm) larger in both dimensions.